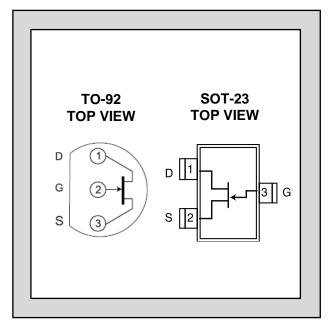


## Twenty-Five Years Of Quality Through Innovation

# **LSK170**

## ULTRA LOW NOISE SINGLE N-CHANNEL JFET AMPLIFIER

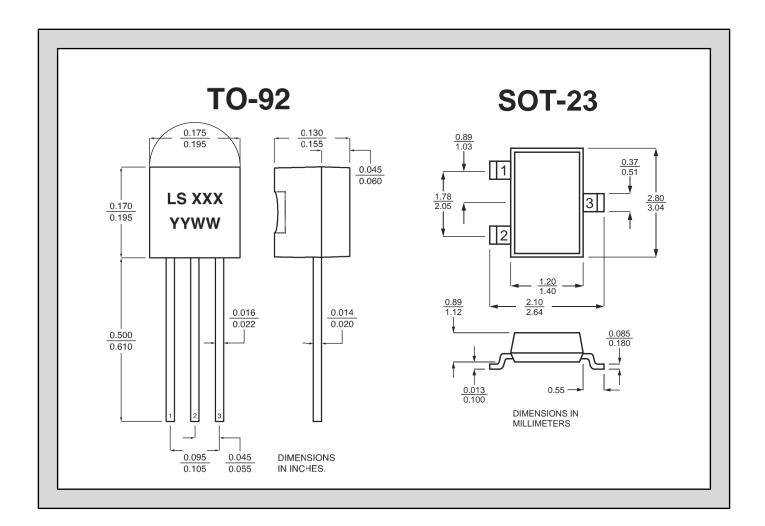
FEATURES						
ULTRA LOW NOISE (f=1kHz)	$e_n = 0.9NV/\sqrt{HZ}$					
HIGH BREAKDOWN VOLTAGE	BV <sub>GSS</sub> =40V max					
HIGH GAIN	Y <sub>fs</sub> =22mS (typ)					
HIGH INPUT IMPEDENCE	I <sub>G</sub> = -500pA max					
LOW CAPACITANCE	22pF max					
IMPROVED SECOND SOURCE REPLACEMENT FOR 2SK170						
ABSOLUTE MAXIMUM RATINGS <sup>1</sup>						
@ 25 °C (unless otherwise stated)						
Maximum Temperatures						
Storage Temperature	-55 to +150 °C					
Operating Junction Temperature	-55 to +135 °C					
Maximum Power Dissipation						
Continuous Power Dissipation@+25°C	400mW					
Maximum Currents						
Gate Forward Current	I <sub>G(F)</sub> = 10mA					
Maximum Voltages						
Gate to Source	V <sub>GSS</sub> = 40V					
Gate to Drain	V <sub>GDS</sub> = 40V					



<sup>\*</sup>For equivalent monolithic dual, see LSK389 family.

#### ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC		MIN	TYP	MAX	UNITS	CONDITIONS	
BV <sub>GSS</sub>	Gate to Source Breakdown Voltage		-40			V	$V_{DS} = 0$ , $I_D = 100 \mu A$	
V <sub>GS(OFF)</sub>	Gate to Source Pinch-off Voltage		-0.2		-2	V	$V_{DS} = 10V$ , $I_D = 1nA$	
$V_{GS}$	Gate to Source Operating Voltage			0.5		V	$V_{DS} = 10V, I_{D} = 1mA$	
Ipss	Drain to Source LS Saturation Current LS	LSK170A	2.6		6.5	mA	V <sub>G</sub> S = 10V, V <sub>G</sub> S = 0	
		LSK170B	6		12			
		LSK170C	10		20			
		LSK170D	18		30			
IG	Gate Operating Current				-0.5	nA	$V_{DG} = 10V$ , $I_D = 1mA$	
I <sub>GSS</sub>	Gate to Source Leakage Current				-1	nA	$V_{GS} = -10V, V_{DS} = 0$	
G <sub>fS</sub>	Full Conduction Transconductance			22		mS	$V_{GD} = 10V$ , $V_{GS} = 0$ , $f = 1kHz$	
GfS	Typical Conduction Transconductance			10		mS	$V_{DG} = 15V$ , $I_D = 1mA$	
<b>e</b> n	Noise Voltage			0.9	1.9	nV/√Hz	$V_{DS} = 10V$ , $I_{D} = 2mA$ , $f = 1kHz$ , $NBW=1Hz$	
<b>e</b> n	Noise Voltage			2.5	4	nV/√Hz	$V_{DS} = 10V$ , $I_{D} = 2mA$ , $f = 10 Hz$ , $NBW=1Hz$	
Ciss	Common Source Input Ca	pacitance		20		pF	$V_{DS} = 15V$ , $I_{D} = 100\mu A$ , $f = 1MHz$	
Crss	Common Source Reverse	Transfer Cap.		5		pF		



### **NOTES:**

- 1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
- 2. Pulse Test: PW ≤ 300µs, Duty Cycle ≤ 3%
- 3. All characteristics MIN/TYP/MAX numbers are absolute values. Negative values indicate electrical polarity only. Information furnished by Linear Integrated Systems is believed to be accurate and reliable. However, no responsibility is assumed for its use; nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Linear Integrated Systems.

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